# IRFP22N50A, SiHFP22N50A

# Vishay Siliconix



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R <sub>thJA</sub>	-	40	
Case-to-Sink, Flat, Greased Surface	R <sub>thCS</sub>	0.24	-	°C/W
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	-	0.45	

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	0 V, I <sub>D</sub> = 250 μA	500	-	-	V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference	e to 25 °C, I <sub>D</sub> = 1 mA	-	0.55	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V	' <sub>GS</sub> = ± 30 V	-	-	± 100	nA
Zava Cata Valtaga Dvain Curvant		V <sub>DS</sub> =	500 V, V <sub>GS</sub> = 0 V	-	-	25	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 400 V	V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	250	μΑ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 13 A <sup>b</sup>	-	-	0.23	Ω
Forward Transconductance	<b>9</b> fs	V <sub>DS</sub> =	50 V, I <sub>D</sub> = 13 A <sup>b</sup>	12	-	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>		$V_{GS} = 0 V$ ,	-	3450	-	
Output Capacitance	C <sub>oss</sub>	,	$V_{GS} = 0 \text{ V},$ $V_{DS} = 25 \text{ V},$ f = 1.0  MHz,  see fig. 5		513	-	
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0			27	-	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 1.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{DS} = 400 \text{ V}, f = 1.0 \text{ MHz}$ $V_{DS} = 400 \text{ V}, f = 1.0 \text{ MHz}$ $V_{DS} = 0 \text{ V to } 400 \text{ V}^{c}$	V <sub>DS</sub> = 1.0 V, f = 1.0 MHz		4935		- pF -
			V <sub>DS</sub> = 400 V, f = 1.0 MHz		137		
Effective Output Capacitance	Coss eff.			264			
Total Gate Charge	$Q_g$		I <sub>D</sub> = 22 A, V <sub>DS</sub> = 400 V, see fig. 6 and 13 <sup>b</sup>	-	-	120	nC
Gate-Source Charge	$Q_{gs}$			-	-	32	
Gate-Drain Charge	$Q_{gd}$		goo ng. o ana 10	-	-	52	
Turn-On Delay Time	t <sub>d(on)</sub>			-	26	-	
Rise Time	t <sub>r</sub>	V <sub>DD</sub> =	250 V, I <sub>D</sub> = 22 A,	-	94	-	no
Turn-Off Delay Time	t <sub>d(off)</sub>		$R_D = 11 \Omega$ , see fig. $10^b$	-	47	-	ns -
Fall Time	t <sub>f</sub>			-	47	-	
Drain-Source Body Diode Characteristic	s		<u> </u>				
Continuous Source-Drain Diode Current	Is	MOSFET symbol showing the integral reverse p - n junction diode		-	-	22	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>			-	-	88	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 22A, V <sub>GS</sub> = 0 V <sup>b</sup>		-	-	1.5	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	- T <sub>J</sub> = 25 °C, I <sub>F</sub> = 22 A, dl/dt = 100 A/μs <sup>b</sup>		-	570	850	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			-	6.1	9.2	μC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-		on in dor	ninatad b	v.L. ond	. \

### Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq$  300  $\mu$ s; duty cycle  $\leq$  2 %.
- c.  $C_{oss}$  eff. is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DS}$ .

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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

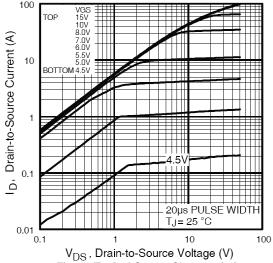


Fig. 1 - Typical Output Characteristics

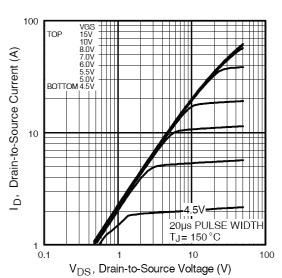


Fig. 2 - Typical Output Characteristics

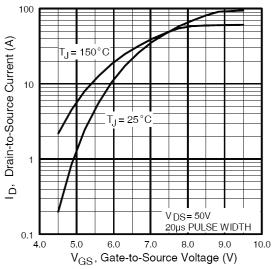


Fig. 3 - Typical Transfer Characteristics

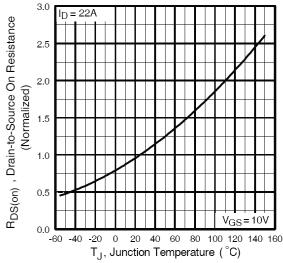


Fig. 4 - Normalized On-Resistance vs. Temperature

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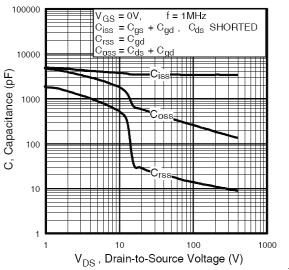


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

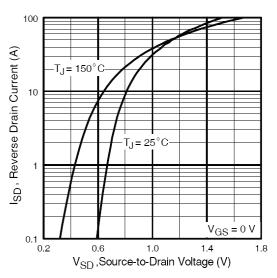


Fig. 7 - Typical Source-Drain Diode Forward Voltage

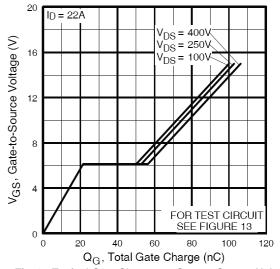


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

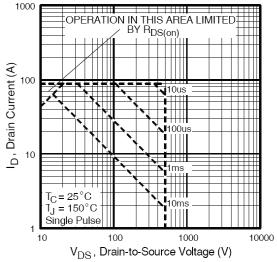


Fig. 8 - Maximum Safe Operating Area



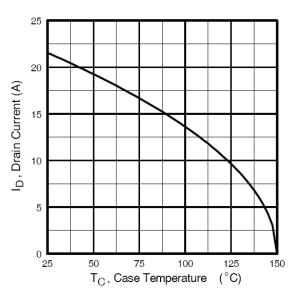


Fig. 9 - Maximum Drain Current vs. Case Temperature

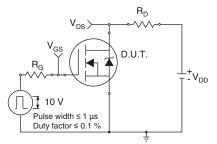


Fig. 10a - Switching Time Test Circuit

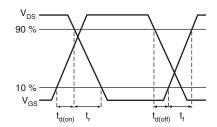


Fig. 10b - Switching Time Waveforms

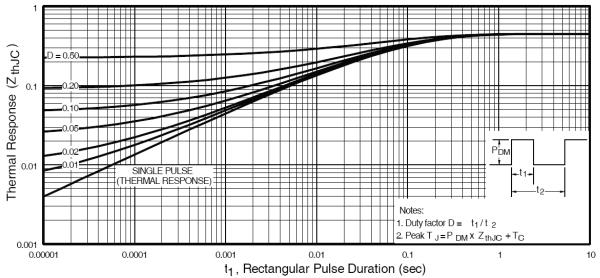


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

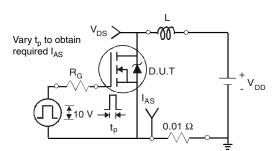


Fig. 12a - Unclamped Inductive Test Circuit

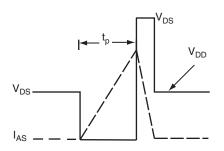


Fig. 12b - Unclamped Inductive Waveforms

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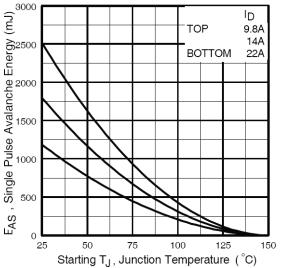


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

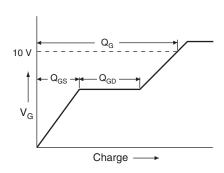


Fig. 13a - Basic Gate Charge Waveform

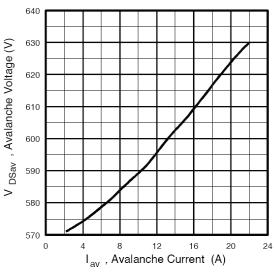


Fig. 12d - Typical Drain-to-Source Voltage vs.
Avalanche Current

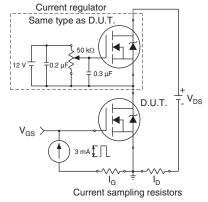
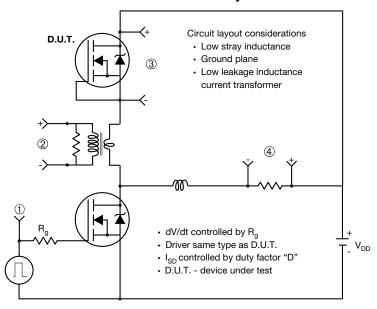


Fig. 13b - Gate Charge Test Circuit

#### Peak Diode Recovery dV/dt Test Circuit



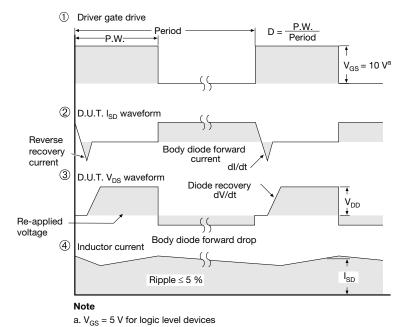


Fig. 14 - For N-Channel

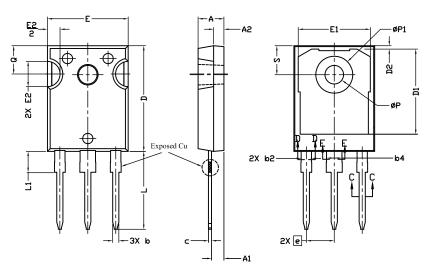
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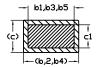


## **TO-247AC (High Voltage)**

#### **VERSION 1: FACILITY CODE = 9**







Section C--C,D--D,E--E

	MILLIN		
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44 BSC		
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

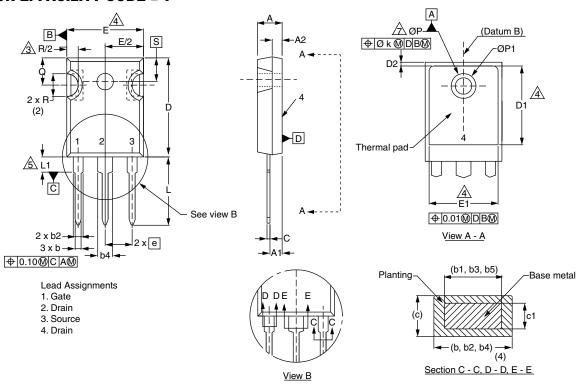
#### Notes

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$  Ø P to have a maximum draft angle of 1.5 $^\circ$  to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

Revision: 19-Oct-2020 1 Document Number: 91360

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#### **VERSION 2: FACILITY CODE = Y**



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	5.46 BSC	
Øk	0.254		
L	14.20	16.25	
L1	3.71	4.29	
ØΡ	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

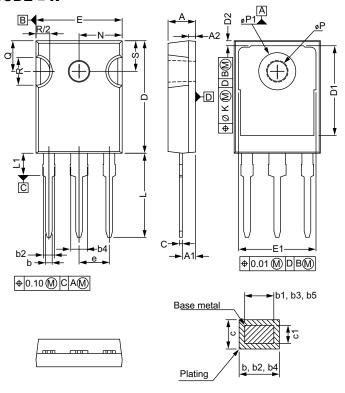
#### **Notes**

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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#### **VERSION 3: FACILITY CODE = N**



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62 BSC		
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

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